

TS256~512MUSD80

80x microSD Memory Card

Description

Transcend microSD Card is non-volatile, which means no external power is required to retain the information stored on it. Besides, it is also a solid-state device that without moving parts to skip or break down. Based on original SLC(Single Level Cell) NAND flash chip, Transcend microSD card can offer an incredible combination of fast data transfer, great flexibility, excellent security and incredibly small size.

Features

- ROHS compliant product
- Operating Voltage: 2.7 ~ 3.6V
- Operating Temperature: -25 ~ 85°C
- Durability: 10,000 insertion/removal cycles
- Fully compatible with SD card spec. v1.1
- Comply with SD Association File System Specification
- Mechanical Write Protection Switch with microSD adapter
- SD Host allows MultiMediaCard upward compatibility
- Form Factor: 11mm x 15mm x 1mm

Placement



Front



Back

Pin Definition

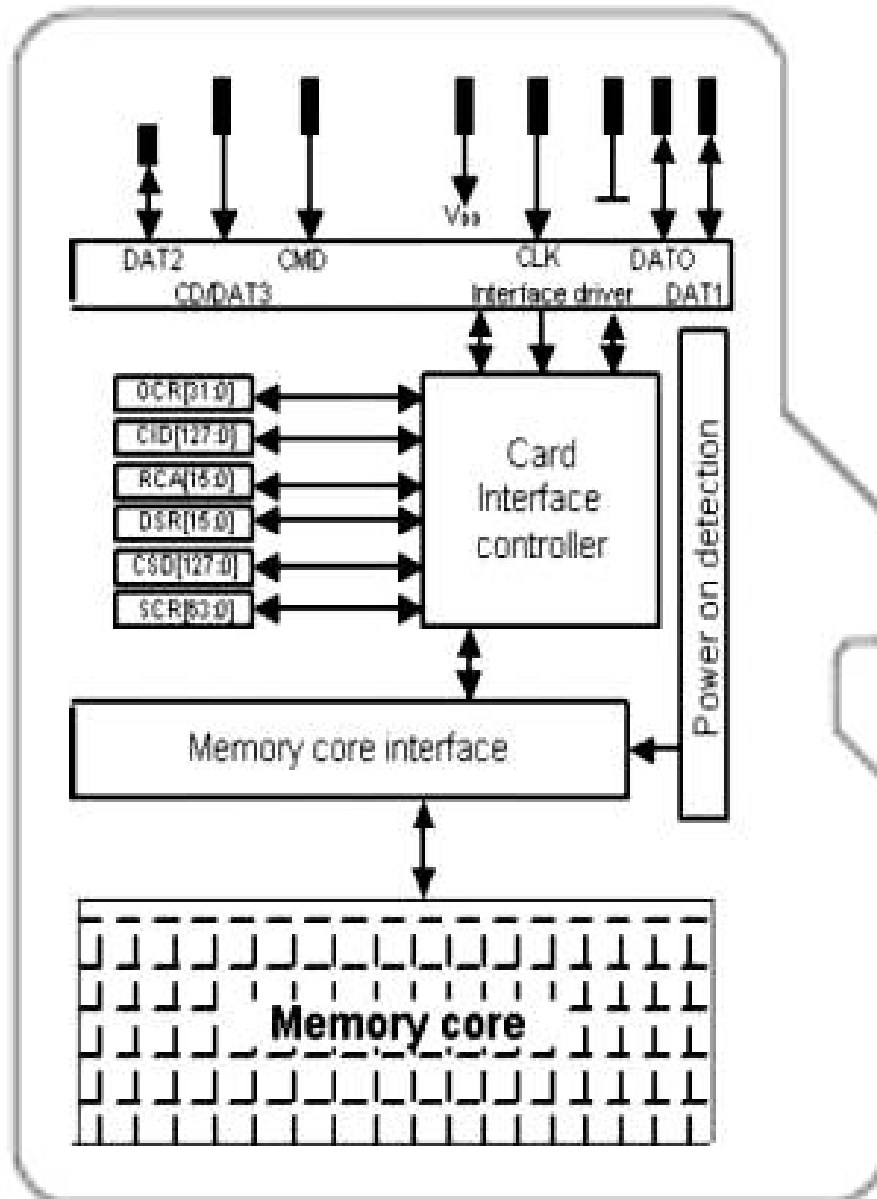
Pin No.	SD Mode			SPI Mode		
	Name	Type	Description	Name	Type	Description
1	DAT2	I/O/PP	Data Line [Bit2]	RSV		Reserved
2	CD/DAT3	I/O/PP	Card Detect / Data Line [Bit3]	CS	I	Chip Select
3	CMD	PP	Command / Response	DI	I	Data In
4	V _{DD}	S	Supply voltage	V _{DD}	S	Supply voltage
5	CLK	I	Clock	SCLK	I	Clock
6	V _{SS}	S	Supply voltage ground	V _{SS}	S	Supply voltage ground
7	DAT0	I/O/PP	Data Line [Bit0]	DO	O/PP	Data out
8	DAT1	I/O/PP	Data Line [Bit1]	RSV		Reserved

S: Power Supply; I:Input; O:Output; PP:Push-Pull

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Architecture



Bus Operating Conditions

• General

Parameter	Symbol	Min.	Max.	Unit	Remark
Peak voltage on all lines		-0.3	VDD+0.3	V	
All Inputs					
Input Leakage Current		-10	10	μA	
All Outputs					
Output Leakage Current		-10	10	μA	

• Power Supply Voltage

Parameter	Symbol	Min.	Max.	Unit	Remark
Supply voltage	V _{DD}	2.0	3.6	V	CMD0, 15,55,ACMD41 commands
Supply voltage specified in OCR register					Except CMD0, 15,55, ACMD41 commands
Supply voltage differentials (V _{SS1} , V _{SS2})		-0.3	0.3	V	
Power up time			250	ms	From 0v to V _{DD} Min.

Note. The current consumption of any card during the power-up procedure must not exceed 10 mA.

• Bus Signal Line Load

The total capacitance C_L the CLK line of the SD Memory Card bus is the sum of the bus master capacitance C_{HOST}, the bus capacitance C_{BUS} itself and the capacitance C_{CARD} of each card connected to this line:

$$C_L = C_{HOST} + C_{BUS} + N \cdot C_{CARD}$$

Where N is the number of connected cards. Requiring the sum of the host and bus capacitances not to exceed 30 pF for up to 10 cards, and 40 pF for up to 30 cards, the following values must not be exceeded:

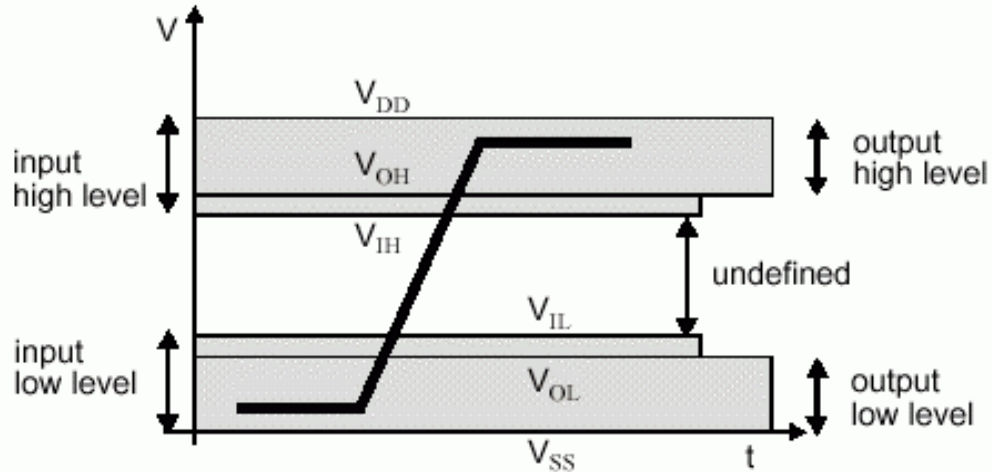
Parameter	Symbol	Min.	Max.	Unit	Remark
Bus signal line capacitance	C _L		100	pF	f _{PP} ≤ 20 MHz, 7 cards
Single card capacitance	C _{CARD}		10	pF	
Maximum signal line inductance			16	nH	f _{PP} ≤ 20 MHz
Pull-up resistance inside card (pin1)	R _{DAT3}	10	90	KΩ	May be used for card detection

Note that the total capacitance of CMD and DAT lines will be consist of C_{HOST}, C_{BUS} and one C_{CARD} only since they are connected separately to the SD Memory Card host.

Parameter	Symbol	Min.	Max.	Unit	Remark
Pull-up resistance	R _{CMD} , R _{DAT}	10	100	KΩ	To prevent bus floating
Bus signal line capacitance	C _L		250	pF	f _{PP} ≤ 5 MHz, 21 cards

• Bus Signal Levels

As the bus can be supplied with a variable supply voltage, all signal levels are related to the supply voltage.



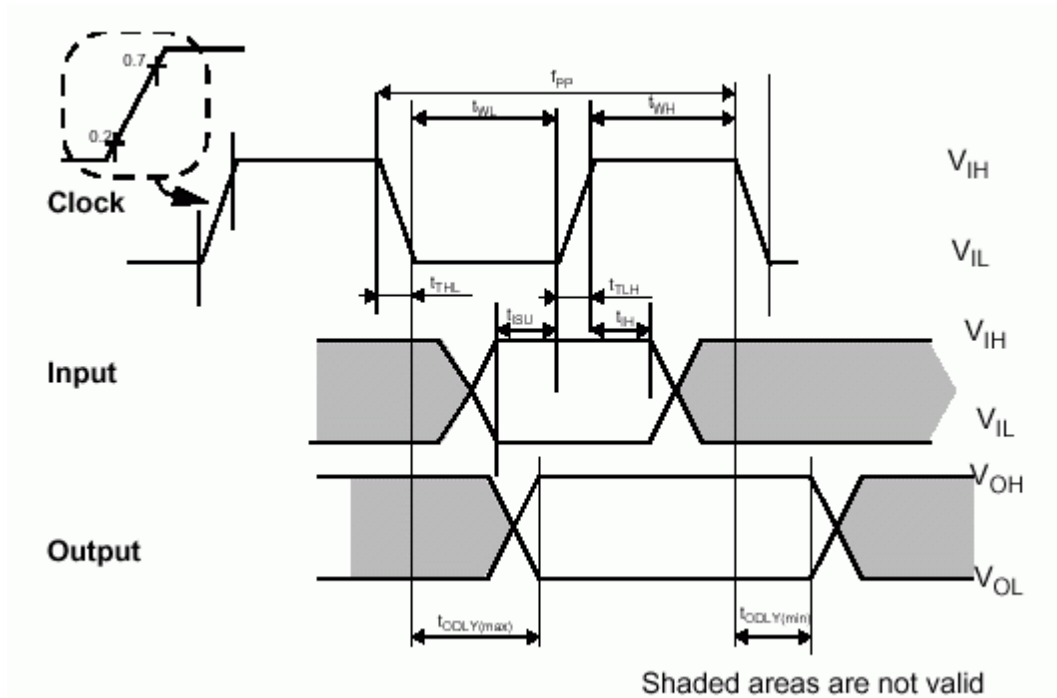
To meet the requirements of the JEDEC specification JESD8-1A, the card input and output voltages shall be within the following specified ranges for any V_{DD} of the allowed voltage range:

Parameter	Symbol	Min.	Max.	Unit	Remark
Output HIGH voltage	V_{OH}	$0.75 * V_{DD}$		V	$I_{OH} = -100 \mu A @ V_{DD} \text{ min}$
Output LOW voltage	V_{OL}		$0.125 * V_{DD}$	V	$I_{OL} = 100 \mu A @ V_{DD} \text{ min}$
Input HIGH voltage	V_{IH}	$0.625 * V_{DD}$	$V_{DD} + 0.3$	V	
Input LOW voltage	V_{IL}	$V_{SS} - 0.3$	$0.25 * V_{DD}$	V	

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• Bus Timing



Parameter	Symbol	Min	Max.	Unit	Remark
Clock CLK (All values are referred to min (V_{IH}) and max (V_{IL}))					
Clock frequency Data Transfer Mode	f_{PP}	0	25	MHz	$C_L \leq 100$ pF, (7 cards)
Clock frequency Identification Mode (The low freq. is required for MultiMediaCard compatibility.)	f_{OD}	0	400	KHz	$C_L \leq 250$ pF, (21 cards)
Clock low time	t_{WL}	10		ns	$C_L \leq 100$ pF, (7 cards)
		50		ns	$C_L \leq 250$ pF, (21 cards)
Clock high time	t_{WH}	10		ns	$C_L \leq 100$ pF, (7 cards)
		50		ns	$C_L \leq 250$ pF, (21 cards)
Clock rise time	t_{TLH}		10	ns	$C_L \leq 100$ pF, (7 cards)
			50	ns	$C_L \leq 250$ pF, (21 cards)
Clock fall time	t_{THL}		10	ns	$C_L \leq 100$ pF, (7 cards)
			50	ns	$C_L \leq 250$ pF, (21 cards)
Inputs CMD, DAT (referenced to CLK)					
Input set-up time	t_{ISU}	5		ns	$C_L \leq 25$ pF, (1 cards)
Input hold time	t_{IH}	5		ns	$C_L \leq 25$ pF, (1 cards)
Outputs CMD, DAT (referenced to CLK)					
Output Delay time	t_{ODLY}	0	14	ns	$C_L \leq 25$ pF, (1 cards)

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Reliability and Durability

Temperature	Operation: -25°C / 85°C (Target spec)
Moisture and corrosion	Operation: 25°C / 95% rel. humidity Storage: 40°C / 93% rel. hum./500h Salt Water Spray: 3% NaCl/35C; 24h acc. MIL STD Method 1009
Durability	10000 mating cycles
Bending	10N
Torque	0.10N*m , +/- 2.5deg max
Drop test	1.5m free fall
UV light exposure	UV: 254nm, 15Ws/cm ² according to ISO 7816-1
Visual inspection Shape and form	No warpage; no mold skin; complete form; no cavities surface smoothness <= -0.1 mm/cm ² within contour; no cracks; no pollution (fat, oil dust, etc.)

Above technical information is based on industry standard data and tested to be reliable. However, Transcend makes no warranty, either expressed or implied, as to its accuracy and assumes no liability in connection with the use of this product. Transcend reserves the right to make changes in specifications at any time without prior notice.